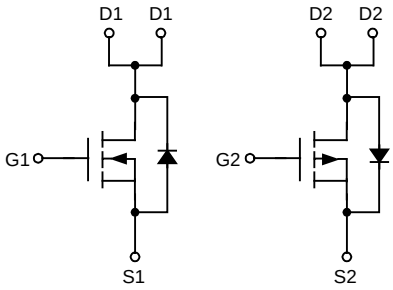
■ PRODUCT CHARACTERISTICS

N-CHANNEL MOSFET		P-CHANNEL MOSFET	
V_{DSS}	40V	V_{DSS}	-40V
$R_{DS(ON)}$ Typ(@V_{GS}=10V)	17mΩ	$R_{DS(ON)}$ Typ(@V_{GS}=-10V)	44mΩ
$R_{DS(ON)}$ Typ(@V_{GS}=4.5V)	22mΩ	$R_{DS(ON)}$ Typ(@V_{GS}=-4.5V)	54mΩ
I_D	9A	I_D	-7.2A

Symbol

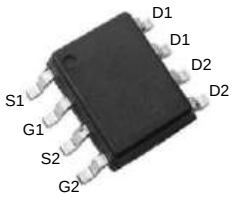


■ APPLICATIONS

* Electronic lamp ballasts based on half bridge
* Load Switching,Quick/Wirelss Charge.
* Motor Driving

■ FEATURE

* Low Gate Charge
* Pb-Free Lead Plating



SOP8

■ ORDER INFORMATION

Order Codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT4615S	SOP8	4000 pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS(T_A=25°C,unless otherwise specified)

Parameter	Symbol	N-channel	P-channel	Unit
Drain-Source Voltage	V_{DSS}	40	-40	V
Gate-Source Voltage	V_{GSS}	±20	±20	V
Drain Current Continuous(@V_{GS}=±10V ,T_A=25°C)	I_D	9	-7.2	A
Drain Current Pulsed	I_{DM}	36	-28.8	A
Avalanche Energy	E_{AS}	42	56	mJ
Power Dissipation	P_D	2		W
Junction Temperature	T_J	+150		°C
Storage Temperature	T_{STG}	-55~ +150		°C

■ THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Unit
Junction to Ambient	R_{thJA}	62.5	°C/W

■ N-MOS ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain to Source Breakdown Voltage	V_{DSS}	V_{GS}=0V,I_D=250μA	40	-	-	V
Drain to Source Leakage Current	I_{DSS}	V_{DS}=40V,V_{GS}=0V	-	-	1	μA
Gate to Source Forward Leakage	$I_{GSS(F)}$	V_{GS}=+20V,V_{DS}=0V	-	-	100	nA
Gate to Source Reverse Leakage	$I_{GSS(R)}$	V_{GS}=-20V ,V_{DS}=0V	-	-	-100	nA
On characteristics						
Drain to Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V,I_D=4.5A	-	17	22	mΩ
		V_{GS}=4.5V,I_D=4.5A	-	22	28	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS},I_D=250μA	1	1.5	2.5	V
Dynamic characteristics						
Gate Resistance	R_g	V_{GS}=0V,V_{DS}=0V ,f=1.0MHz	-	2.8	-	Ω
Forward Transconductance	g_{fs}	V_{DS}=10V,I_D=3A	-	12	-	S
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V f=1.0MHz	-	980	-	pF
Output Capacitance	C_{oss}		-	65	-	pF
Reverse Transfer Capacitance	C_{rss}		-	55	-	pF
Resistive Switching Characteristics						
Turn-on Delay Time	$t_{d(ON)}$	V_{GS}=10V, V_{DS}=20V, I_D=9A,R_G=3Ω	-	4	-	ns
Rise Time	t_r		-	3	-	ns
Turn-off Delay Time	$t_{d(OFF)}$		-	15	-	ns
Fall Time	t_f		-	2	-	ns
Total Gate Charge	Q_g	I_D=9A, V_{DS}=20V V_{GS}=10V	-	12	-	nC
Gate to Source Charge	Q_{gs}		-	3.2	-	nC
Gate to Drain("Miller") Charge	Q_{gd}		-	3.1	-	nC
Source-Drain Diode Characteristics						
Continuous Source Current(Body Diode)	I_S		-	-	9	A
Maximum Pulsed Current(Body Diode)	I_{SM}		-	-	36	A
Diode Forward Voltage	V_{SD}	I_{SD}=1A, V_{GS}=0V	-	0.74	1.2	V

■ P-MOS ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain to Source Breakdown Voltage	V_{DSS}	V_{GS}=0V,I_D=-250μA	-40	-	-	V
Drain to Source Leakage Current	I_{DSS}	V_{DS}=-40V,V_{GS}=0V	-	-	-1	μA
Gate to Source Forward Leakage	$I_{GSS(F)}$	V_{GS}=+20V,V_{DS}=0V	-	-	100	nA
Gate to Source Reverse Leakage	$I_{GSS(R)}$	V_{GS}=-20V ,V_{DS}=0V	-	-	-100	nA
On characteristics						
Drain to Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-10V,I_D=-3.6A	-	44	50	mΩ
		V_{GS}=-4.5V,I_D=-3.6A	-	54	65	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS},I_D=-250μA	-1	-1.5	-2.4	V
Dynamic characteristics						
Gate Resistance	R_g	V_{GS}=0V,V_{DS}=0V ,f=1.0MHz	-	6.4	-	Ω
Forward Transconductance	g_{fs}	V_{DS}=-5V,I_D=-5A	-	10	-	S
Input Capacitance	C_{iss}	V_{DS}=-20V,V_{GS}=0V f=1.0MHz	-	890	-	pF
Output Capacitance	C_{oss}		-	80	-	pF
Reverse Transfer Capacitance	C_{rss}		-	60	-	pF
Resistive Switching Characteristics						
Turn-on Delay Time	$t_{d(ON)}$	V_{GS}=-10V,V_{DS}=-20V, I_D=-2A ,R_G=25Ω	-	6	-	ns
Rise Time	t_r		-	8	-	ns
Turn-off Delay Time	$t_{d(OFF)}$		-	2.1	-	ns
Fall Time	t_f		-	3.6	-	ns
Total Gate Charge	Q_g	I_D=-2A, V_{GS}=-10V V_{DS}=-20V	-	20	-	nC
Gate to Source Charge	Q_{gs}		-	12	-	nC
Gate to Drain("Miller") Charge	Q_{gd}		-	46	-	nC
Source-Drain Diode Characteristics						
Continuous Source Current(Body Diode)	I_S		-	-	-7.2	A
Maximum Pulsed Current(Body Diode)	I_{SM}		-	-	-28.8	A
Diode Forward Voltage	V_{SD}	I_{SD}=-1A, V_{GS}=0V	-	-0.74	-1.2	V

■ N-MOS TYPICAL CHARACTERISTICS

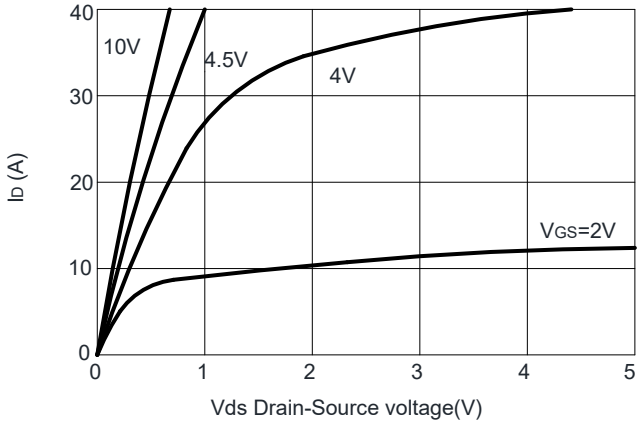


Figure 1: Output Characteristics

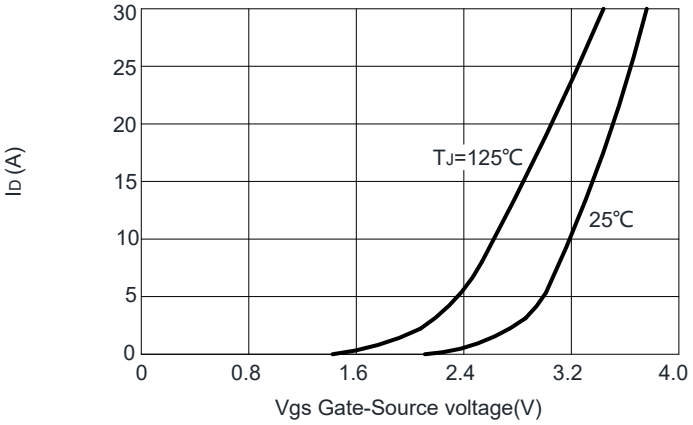


Figure 2: Transfer Characteristics

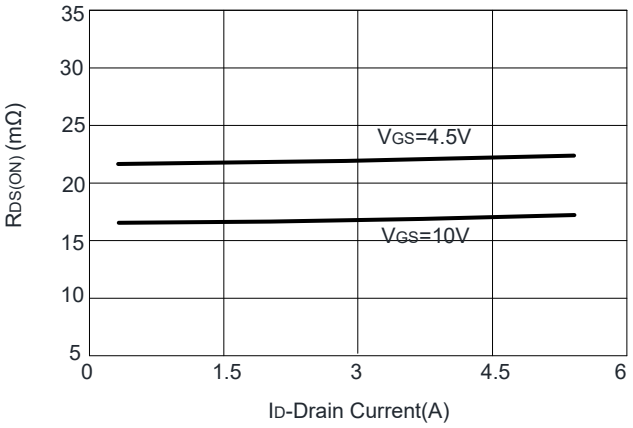


Figure 3: On-Resistance vs.Drain Current

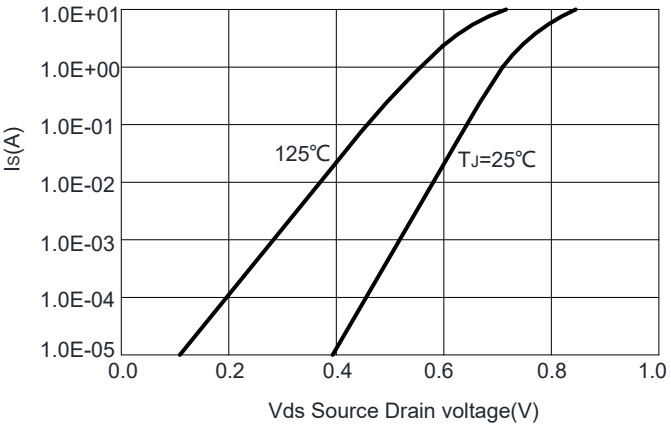


Figure 4: Body diode Characteristics

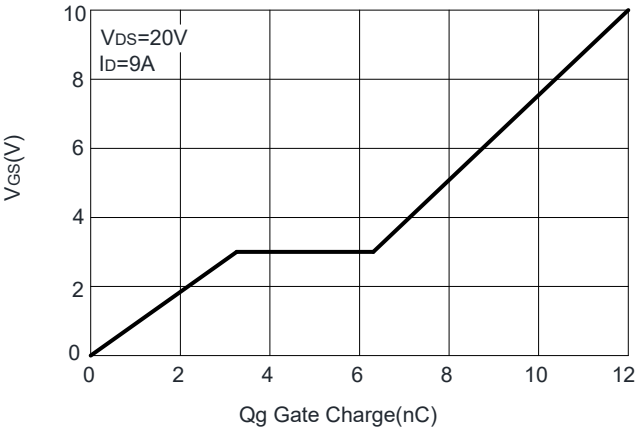


Figure 5: Gate Charge Characteristics

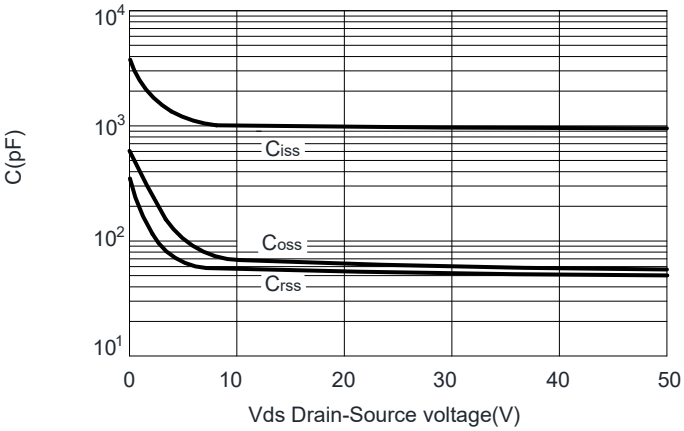


Figure 6: Capacitance Characteristics

■ N-MOS TYPICAL CHARACTERISTICS(Cont.)

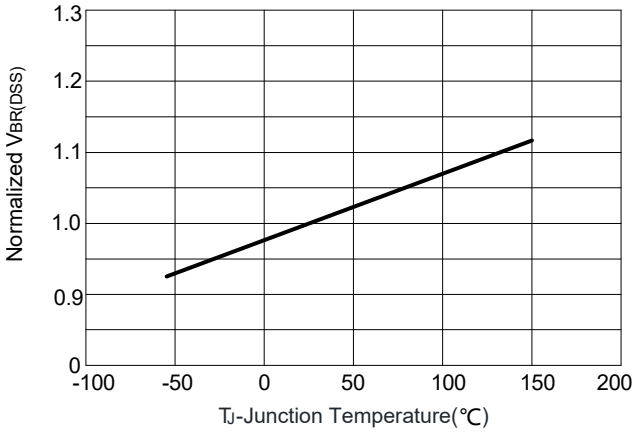


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

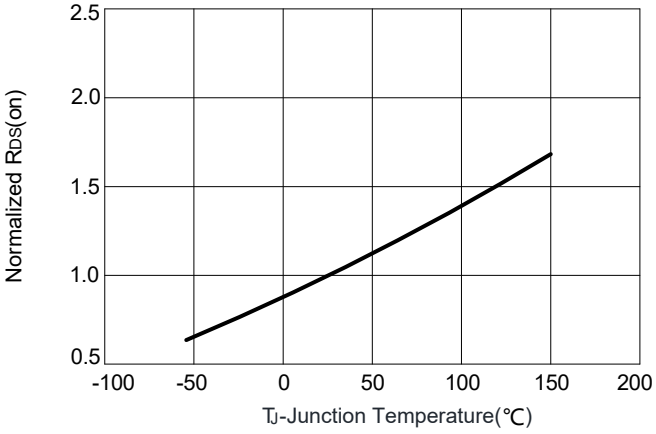


Figure 8: Normalized On-resistance vs. Junction Temperature

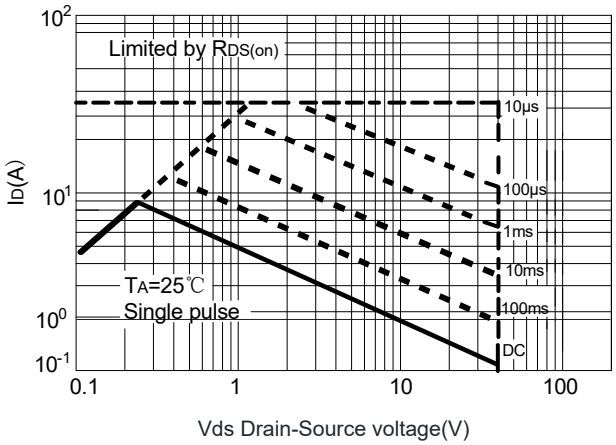


Figure 9: Maximum Safe Operating Area

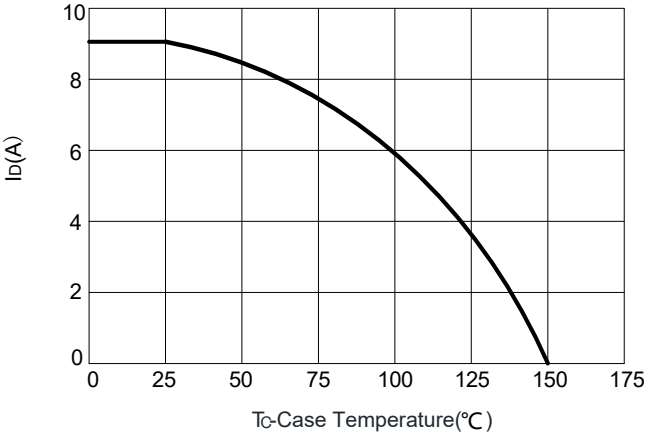


Figure 10: Mximum Continuous Drain Current vs. Case Temperature

■ P-MOS TYPICAL CHARACTERISTICS

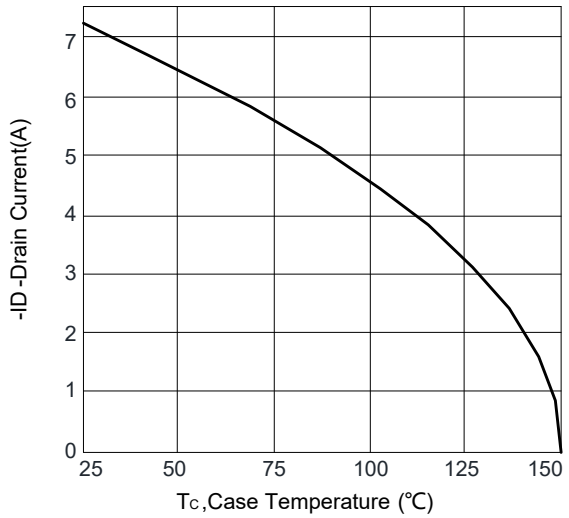


Figure 1:Continuous Drain Current vs.Tc

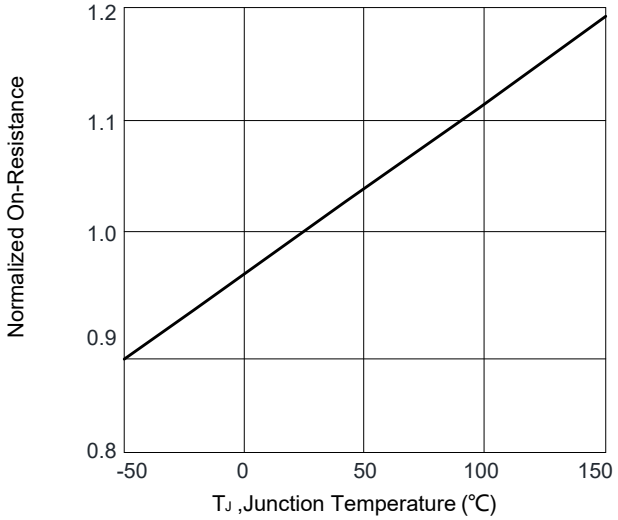


Figure 2:Normalized Rdsont vs.TJ

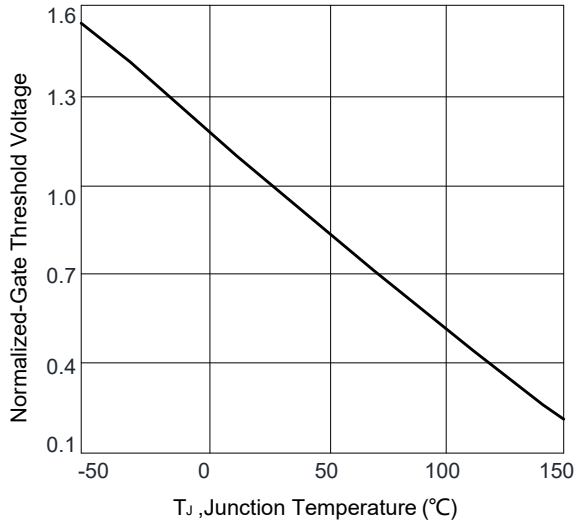


Figure 3:Normalized V_{th} vs. T_J

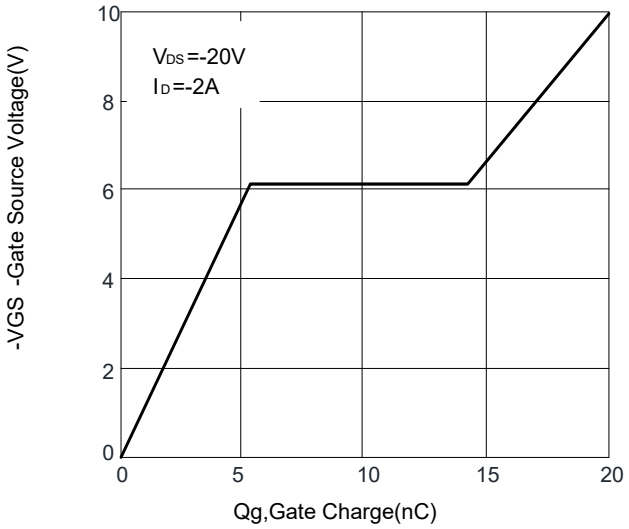


Figure 4:Gate Charge Waveform

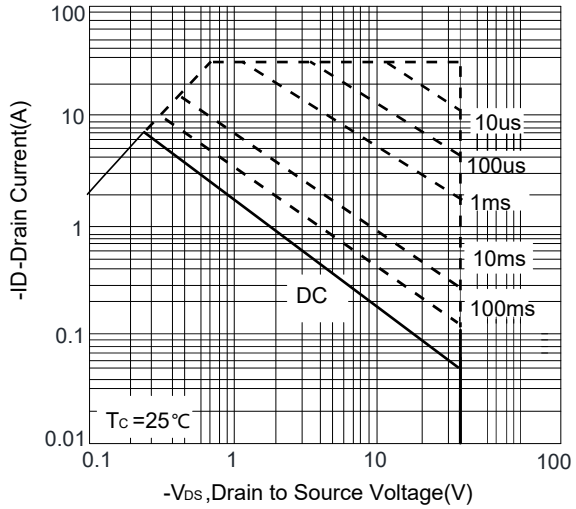
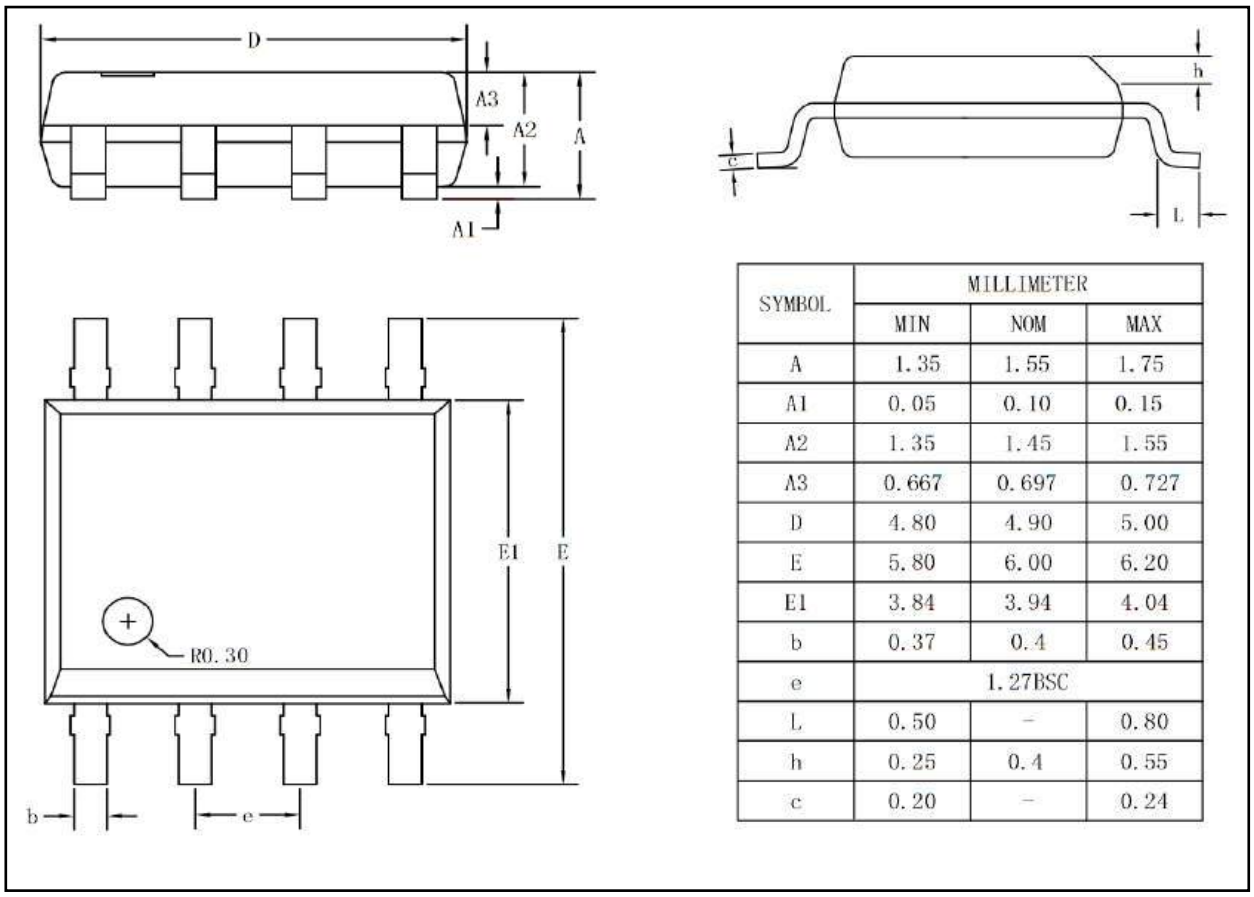


Figure 5:Maximum Safe Operation Area

■ SOP8 PACKAGE OUTLINE DIMENSIONS



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.05	0.10	0.15
A2	1.35	1.45	1.55
A3	0.667	0.697	0.727
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.84	3.94	4.04
b	0.37	0.4	0.45
e	1.27BSC		
L	0.50	-	0.80
h	0.25	0.4	0.55
c	0.20	-	0.24